

Technische Information / Technical Information

IGBT-Module
IGBT-Modules

BSM100GP60

eupec



Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Diode Gleichrichter/ Diode Rectifier

Periodische Rückw. Spitzensperrespannung repetitive peak reverse voltage		V_{RRM}	1600	V
Durchlaßstrom Grenzeffektivwert RMS forward current per chip		I_{FRMSM}	80	A
Dauergleichstrom DC forward current	$T_C = 80^\circ\text{C}$	I_d	100	A
Stoßstrom Grenzwert surge forward current	$t_p = 10\text{ ms}, T_{vj} = 25^\circ\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^\circ\text{C}$	I_{FSM}	700 570	A A
Grenzlastintegral I^2t - value	$t_p = 10\text{ ms}, T_{vj} = 25^\circ\text{C}$ $t_p = 10\text{ ms}, T_{vj} = 150^\circ\text{C}$	I^2t	2450 1620	A^2s A^2s

Transistor Wechselrichter/ Transistor Inverter

Kollektor-Emitter-Sperrespannung collector-emitter voltage		V_{CES}	600	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 70^\circ\text{C}$ $T_C = 25^\circ\text{C}$	$I_{C,nom.}$ I_C	100 135	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 70^\circ\text{C}$	I_{CRM}	200	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$	P_{tot}	420	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Wechselrichter/ Diode Inverter

Dauergleichstrom DC forward current	$T_C = 70^\circ\text{C}$	I_F	100	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	200	A
Grenzlastintegral I^2t - value	$V_R = 0\text{V}, t_p = 10\text{ms}, T_{vj} = 125^\circ\text{C}$	I^2t	2.300	A^2s

Transistor Brems-Chopper/ Transistor Brake-Chopper

Kollektor-Emitter-Sperrespannung collector-emitter voltage		V_{CES}	600	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^\circ\text{C}$ $T_C = 25^\circ\text{C}$	$I_{C,nom.}$ I_C	50 75	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}, T_C = 80^\circ\text{C}$	I_{CRM}	100	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^\circ\text{C}$	P_{tot}	250	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Brems-Chopper/ Diode Brake-Chopper

Dauergleichstrom DC forward current	$T_C = 70^\circ\text{C}$	I_F	30	A
Periodischer Spitzenstrom repetitive peak forw. current	$t_p = 1\text{ ms}$	I_{FRM}	60	A

prepared by: Andreas Schulz

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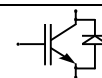
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Modul Isolation/ Module Isolation

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min. NTC connected to Baseplate	V_{ISOL}	2,5	kV
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Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

Diode Gleichrichter/ Diode Rectifier		min.	typ.	max.	
Durchlaßspannung forward voltage	$T_{vj} = 150^{\circ}\text{C}$, $I_F = 100\text{ A}$	V_F	-	1,16	V
Schleusenspannung threshold voltage	$T_{vj} = 150^{\circ}\text{C}$	$V_{(TO)}$	-	-	0,8 V
Ersatzwiderstand slope resistance	$T_{vj} = 150^{\circ}\text{C}$	r_T	-	-	4,8 mΩ
Sperrstrom reverse current	$T_{vj} = 150^{\circ}\text{C}$, $V_R = 1600\text{ V}$	I_R	-	4	mA
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	$T_C = 25^{\circ}\text{C}$	$R_{AA'+CC'}$	-	4	mΩ

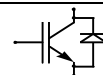
Transistor Wechselrichter/ Transistor Inverter		min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$V_{GE} = 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $I_C = 100\text{ A}$	$V_{CE\text{ sat}}$	-	1,95	V
	$V_{GE} = 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $I_C = 100\text{ A}$		-	2,2	V
Gate-Schwellenspannung gate threshold voltage	$V_{CE} = V_{GE}$, $T_{vj} = 25^{\circ}\text{C}$, $I_C = 1,5\text{ mA}$	$V_{GE(TO)}$	4,5	5,5	6,5 V
Eingangskapazität input capacitance	f = 1MHz, $T_{vj} = 25^{\circ}\text{C}$ $V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$	C_{ies}	-	4,3	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{GE} = 0\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $V_{CE} = 600\text{ V}$	I_{CES}	-	3,0	μA
	$V_{GE} = 0\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $V_{CE} = 600\text{ V}$		-	4,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$, $T_{vj} = 25^{\circ}\text{C}$	I_{GES}	-	-	300 nA
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	$t_{d,on}$	-	50	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	t_r	-	65	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	$t_{d,off}$	-	260	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
Fallzeit (induktive Last) fall time (inductive load)	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	t_f	-	35	ns
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 25^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	E_{on}	-	4,2	mWs
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
	$L_S = 50\text{ nH}$				
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = I_{Nenn}$, $V_{CC} = 300\text{ V}$	E_{off}	-	3,2	mWs
	$V_{GE} = \pm 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $R_G = 15\text{ Ohm}$				
	$L_S = 50\text{ nH}$				
Kurzschlußverhalten SC Data	$t_P \leq 10\mu\text{s}$, $V_{GE} \leq 15\text{V}$, $R_G = 15\text{ Ohm}$ $T_{vj} \leq 125^{\circ}\text{C}$, $V_{CC} = 360\text{ V}$ $di/dt = 4000\text{ A}/\mu\text{s}$	I_{SC}	-	400	A

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Charakteristische Werte / Characteristic values

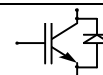
			min.	typ.	max.	
Modulinduktivität stray inductance module		$L_{\sigma CE}$	-	-	100	nH
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	$T_C = 25^\circ\text{C}$	R_{CC+EE}	-	7	-	mΩ
Diode Wechselrichter/ Diode Inverter			min.	typ.	max.	
Durchlaßspannung forward voltage	$V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}, I_F = 100\text{ A}$ $V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}, I_F = 100\text{ A}$	V_F	-	1,25 1,2	1,7 -	V V
Rückstromspitze peak reverse recovery current	$I_F = I_{Nenn}, -di_F/dt = 2200\text{A}/\mu\text{s}$ $V_{GE} = -10\text{V}, T_{vj} = 25^\circ\text{C}, V_R = 300\text{ V}$ $V_{GE} = -10\text{V}, T_{vj} = 125^\circ\text{C}, V_R = 300\text{ V}$	I_{RM}	- -	68 90	- -	A A
Sperrverzögerungsladung recovered charge	$I_F = I_{Nenn}, -di_F/dt = 2200\text{A}/\mu\text{s}$ $V_{GE} = -10\text{V}, T_{vj} = 25^\circ\text{C}, V_R = 300\text{ V}$ $V_{GE} = -10\text{V}, T_{vj} = 125^\circ\text{C}, V_R = 300\text{ V}$	Q_r	- -	6,2 10,5	- -	μAs μAs
Abschaltenergie pro Puls reverse recovery energy	$I_F = I_{Nenn}, -di_F/dt = 2200\text{A}/\mu\text{s}$ $V_{GE} = -10\text{V}, T_{vj} = 25^\circ\text{C}, V_R = 300\text{ V}$ $V_{GE} = -10\text{V}, T_{vj} = 125^\circ\text{C}, V_R = 300\text{ V}$	E_{RQ}	- -	1,3 2,2	- -	mWs mWs
Transistor Brems-Chopper/ Transistor Brake-Chopper			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$V_{GE} = 15\text{V}, T_{vj} = 25^\circ\text{C}, I_C = 50,0\text{ A}$ $V_{GE} = 15\text{V}, T_{vj} = 125^\circ\text{C}, I_C = 50,0\text{ A}$	$V_{CE sat}$	- -	1,95 2,2	2,55 -	V V
Gate-Schwellenspannung gate threshold voltage	$V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}, I_C = 1\text{ mA}$	$V_{GE(TH)}$	4,5	5,5	6,5	V
Eingangskapazität input capacitance	$f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}$ $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{ies}	-	2,8	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{GE} = 0\text{V}, T_{vj} = 25^\circ\text{C}, V_{CE} = 600\text{ V}$ $V_{GE} = 0\text{V}, T_{vj} = 125^\circ\text{C}, V_{CE} = 600\text{ V}$	I_{CES}	- -	1,5 2,0	500 -	μA mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{V}, V_{GE} = 20\text{V}, T_{vj} = 25^\circ\text{C}$	I_{GES}	-	-	300	nA
Diode Brems-Chopper/ Diode Brake-Chopper			min.	typ.	max.	
Durchlaßspannung forward voltage	$T_{vj} = 25^\circ\text{C}, I_F = 50,0\text{ A}$ $T_{vj} = 125^\circ\text{C}, I_F = 50,0\text{ A}$	V_F	- -	1,45 1,4	1,8 -	V V
NTC-Widerstand/ NTC-Thermistor			min.	typ.	max.	
Nennwiderstand rated resistance	$T_C = 25^\circ\text{C}$	R_{25}	-	5	-	kΩ
Abweichung von R_{100} deviation of R_{100}	$T_C = 100^\circ\text{C}, R_{100} = 493\text{ Ω}$	$\Delta R/R$	-5		5	%
Verlustleistung power dissipation	$T_C = 25^\circ\text{C}$	P_{25}			20	mW
B-Wert B-value	$R_2 = R_1 \exp [B(1/T_2 - 1/T_1)]$	$B_{25/50}$		3375		K

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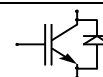


Thermische Eigenschaften / Thermal properties

			min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Gleichr. Diode/ Rectif. Diode	R_{thJC}	-	-	0,5	K/W
	Trans. Wechsr./ Trans. Inverter		-	-	0,3	K/W
	Diode Wechsr./ Diode Inverter		-	-	0,5	K/W
	Trans. Bremse/ Trans. Brake		-	-	0,5	K/W
	Diode Bremse/ Diode Brake		-	-	1,2	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	Gleichr. Diode/ Rectif. Diode	$\lambda_{paste}=1W/m^2K$ R_{thCK}	-	0,04	-	K/W
	Trans. Wechsr./ Trans. Inverter	$\lambda_{grease}=1W/m^2K$	-	0,02	-	K/W
	Diode Wechsr./ Diode Inverter		-	0,04	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature		T_{op}	-40	-	125	°C
Lagertemperatur storage temperature		T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

Innere Isolation internal insulation			Al_2O_3	
CTI comperative tracking index			225	
Anzugsdrehmoment f. mech. Befestigung mounting torque		M	3 ±10%	Nm
Gewicht weight		G	300	g

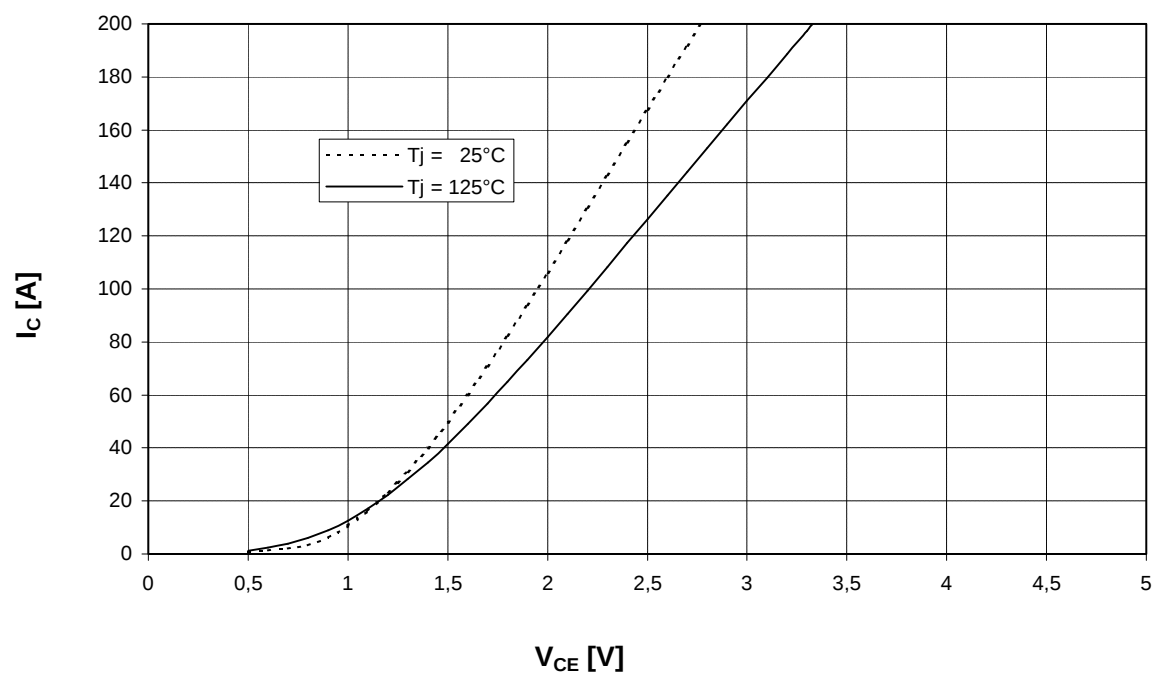


Ausgangskennlinienfeld Wechselr. (typisch)

Output characteristic Inverter (typical)

$$I_C = f(V_{CE})$$

$$V_{GE} = 15 \text{ V}$$

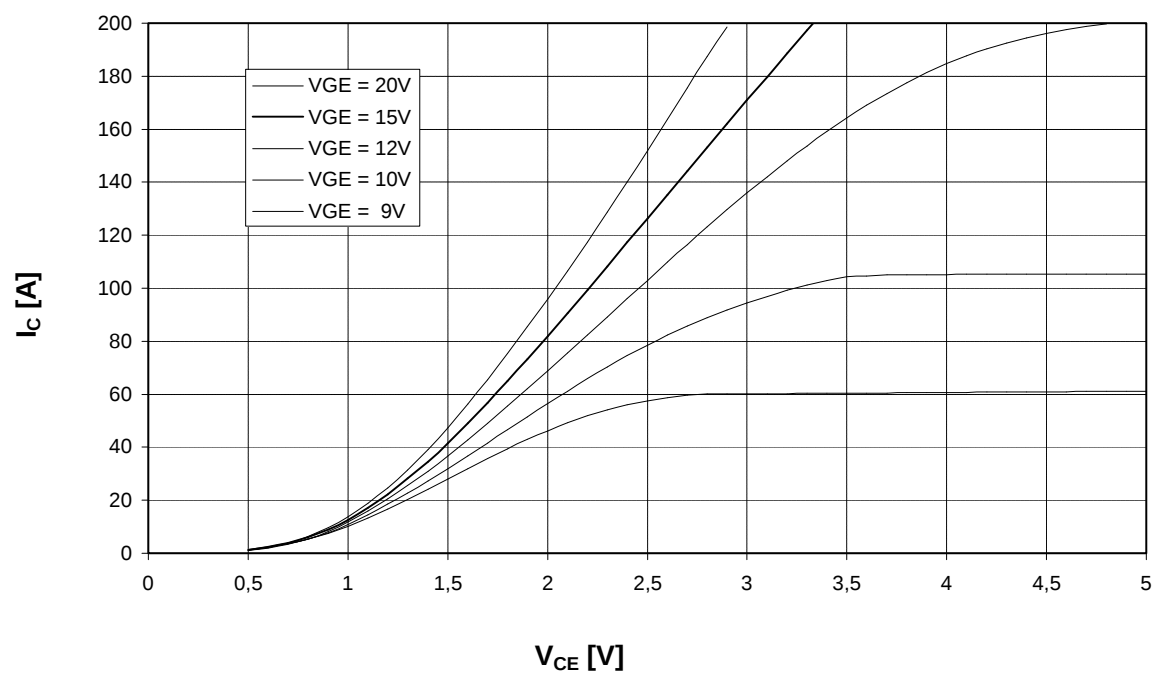


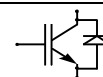
Ausgangskennlinienfeld Wechselr. (typisch)

Output characteristic Inverter (typical)

$$I_C = f(V_{CE})$$

$$T_{vj} = 125^\circ\text{C}$$



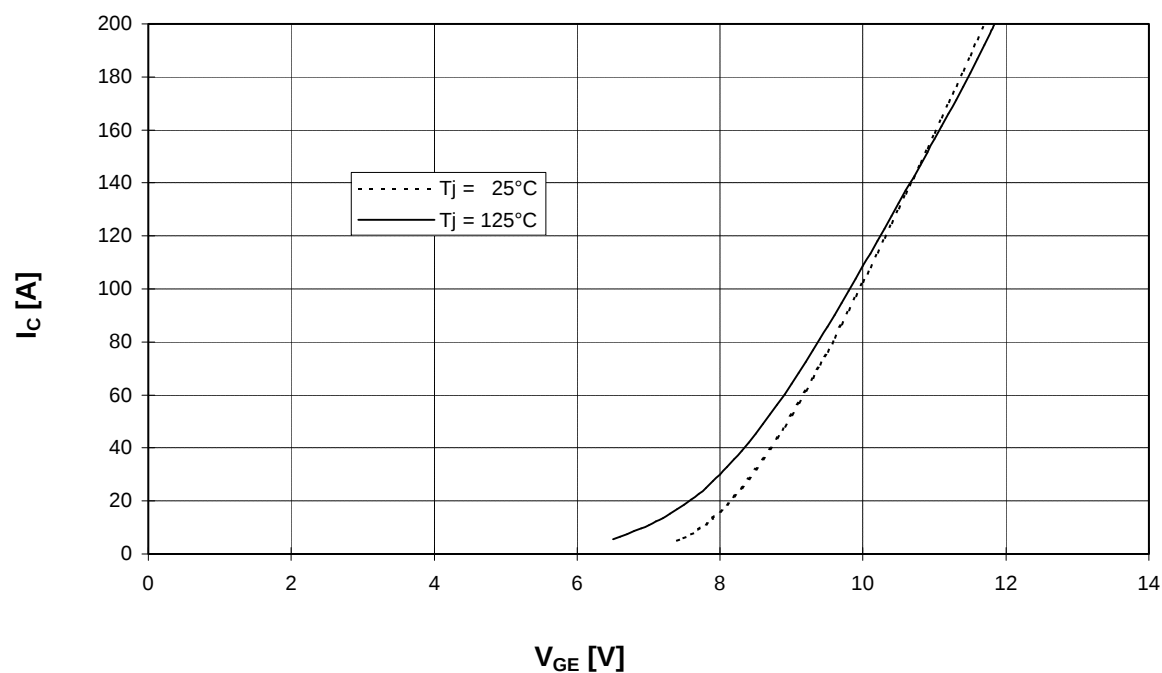


Übertragungscharakteristik Wechselr. (typisch)

Transfer characteristic Inverter (typical)

$$I_C = f(V_{GE})$$

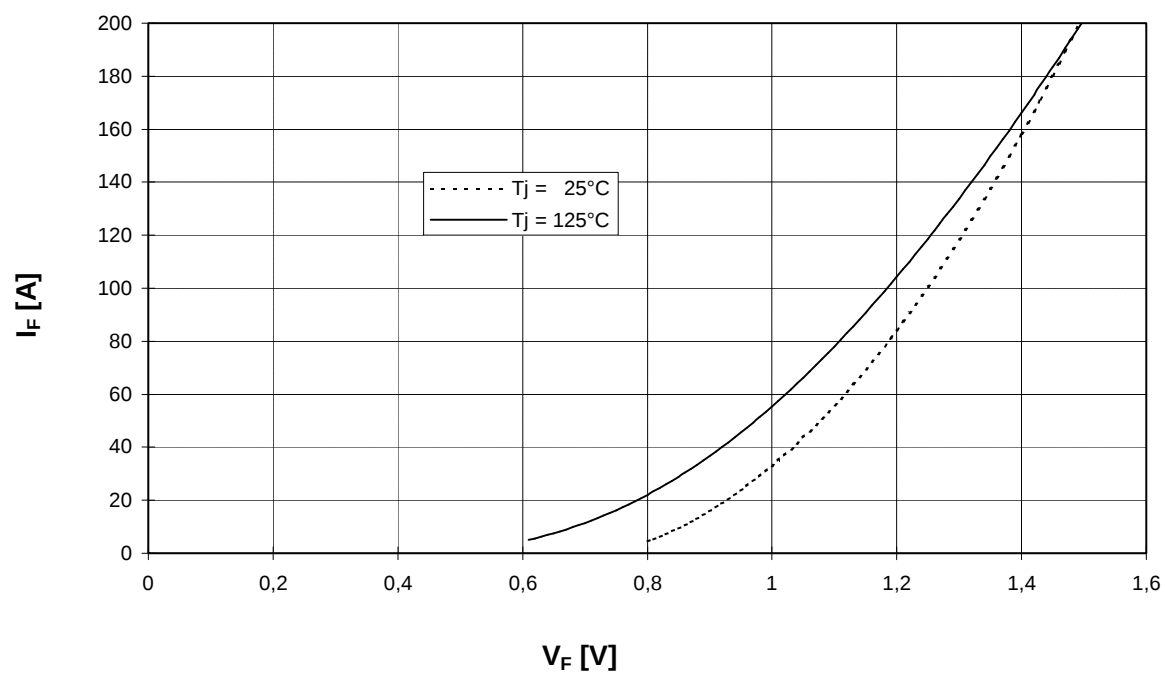
$$V_{CE} = 20 \text{ V}$$

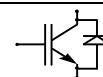


Durchlaßkennlinie der Freilaufdiode Wechselr. (typisch)

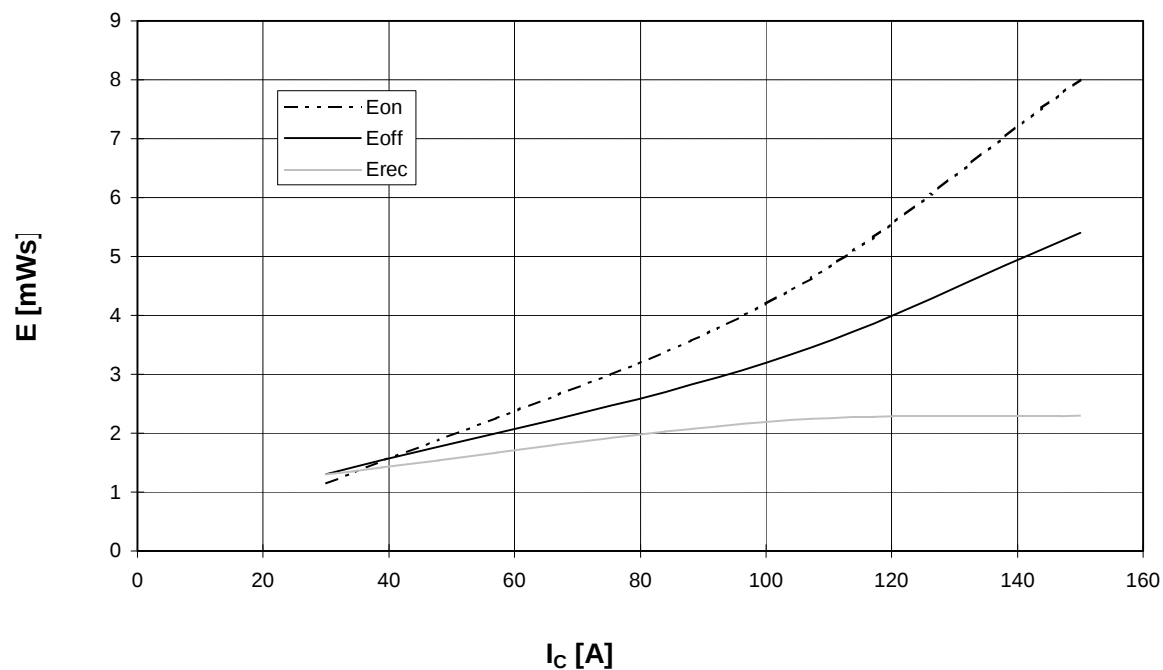
Forward characteristic of FWD Inverter (typical)

$$I_F = f(V_F)$$

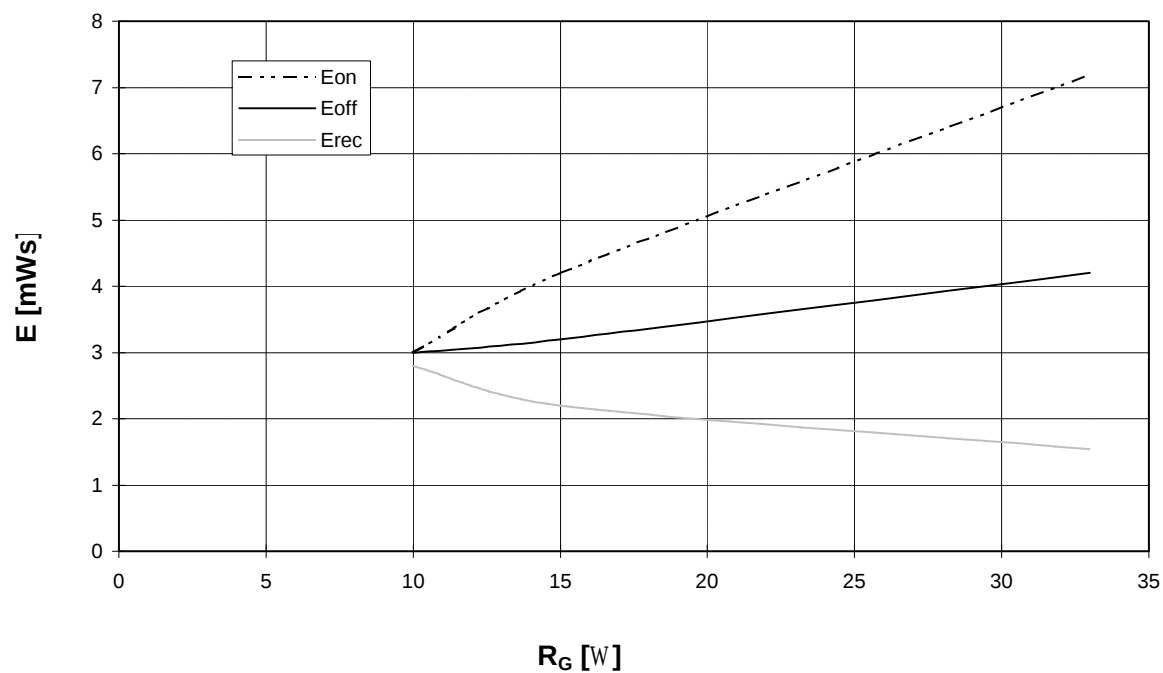


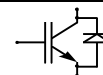


Schaltverluste Wechselr. (typisch) $E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$ $V_{CC} = 300\text{ V}$
Switching losses Inverter (typical) $T_j = 125^\circ\text{C}$, $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = R_{Goff} = 15\text{ Ohm}$



Schaltverluste Wechselr. (typisch) $E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$
Switching losses Inverter (typical) $T_j = 125^\circ\text{C}$, $V_{GE} = \pm 15\text{ V}$, $I_C = I_{nenn}$, $V_{CC} = 300\text{ V}$

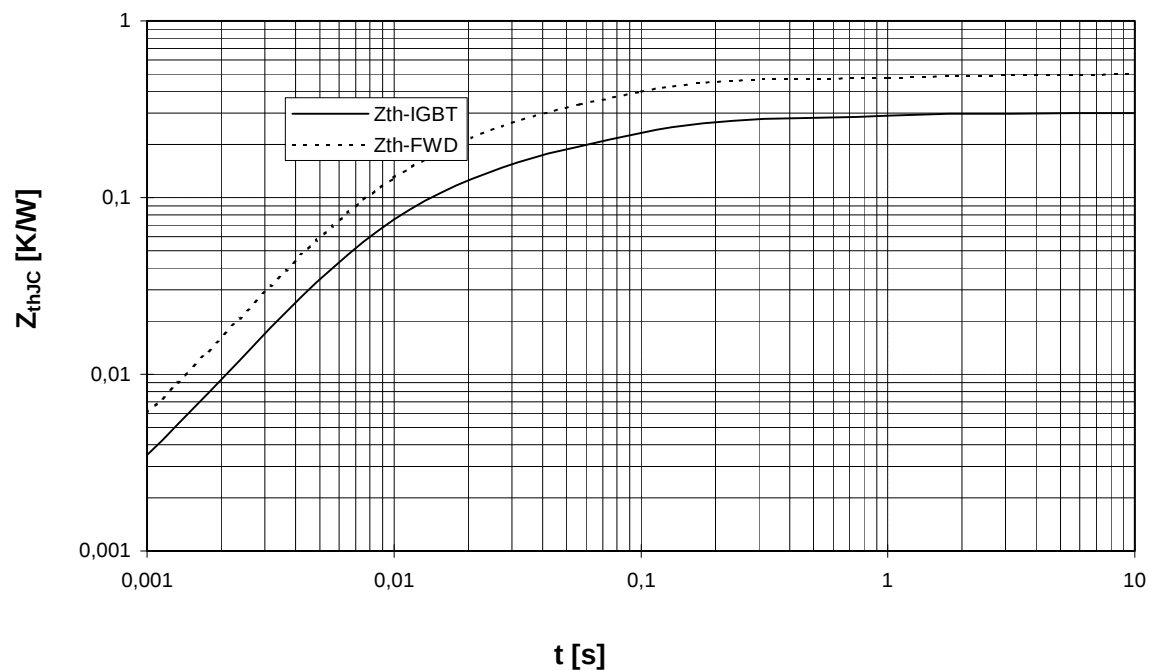




Transienter Wärmewiderstand Wechsellr.

$$Z_{thJC} = f(t)$$

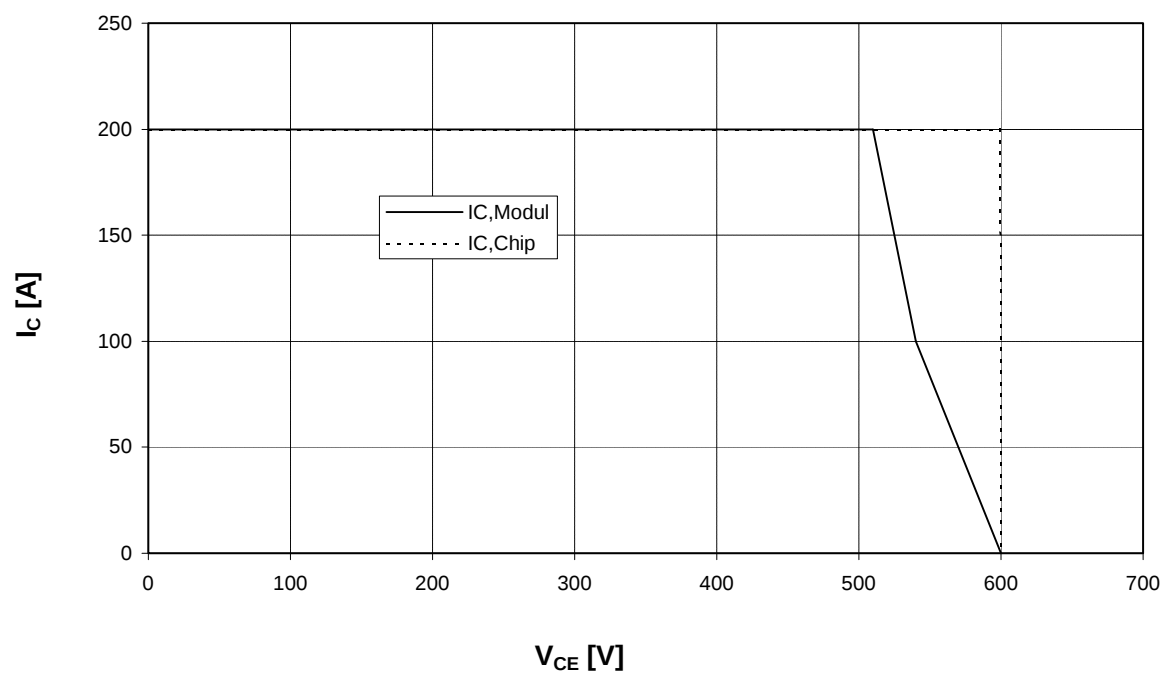
Transient thermal impedance Inverter

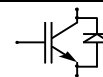


Sicherer Arbeitsbereich Wechsellr. (RBSOA)

$$I_C = f(V_{CE})$$

Reverse bias safe operating area Inverter (RBSOA) $T_{vj} = 125^\circ C$, $V_{GE} = \pm 15V$, $R_G = 15 \text{ Ohm}$



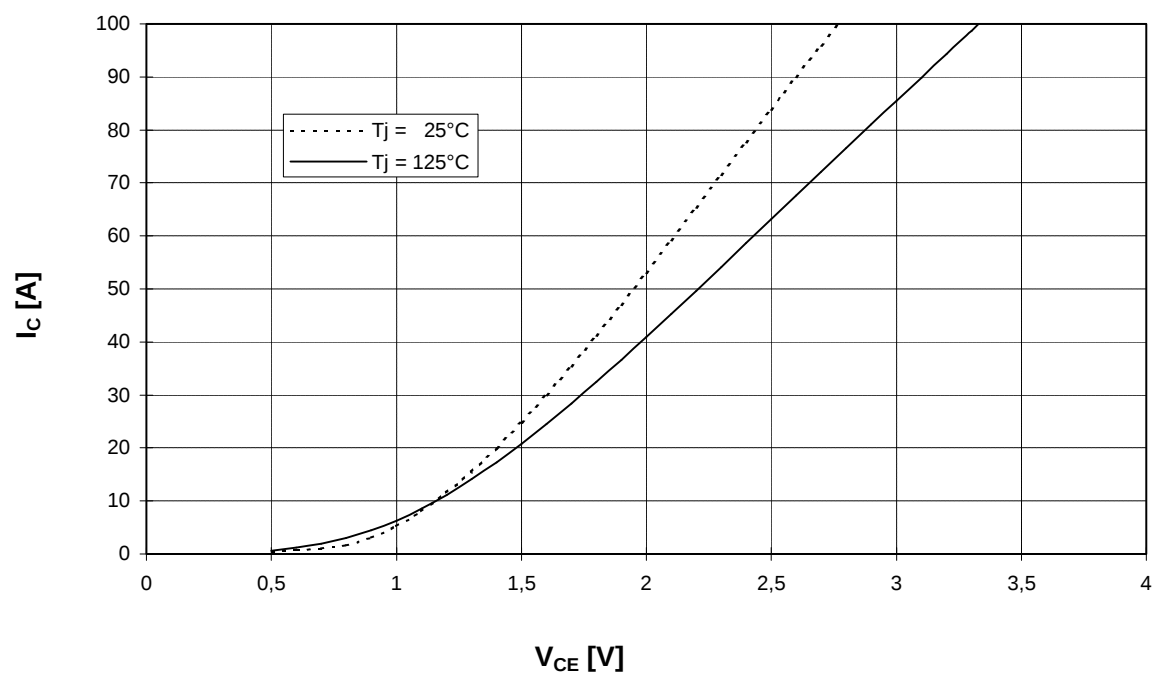


Ausgangskennlinienfeld Brems-Chopper-IGBT (typisch)

Output characteristic brake-chopper-IGBT (typical)

$$I_C = f(V_{CE})$$

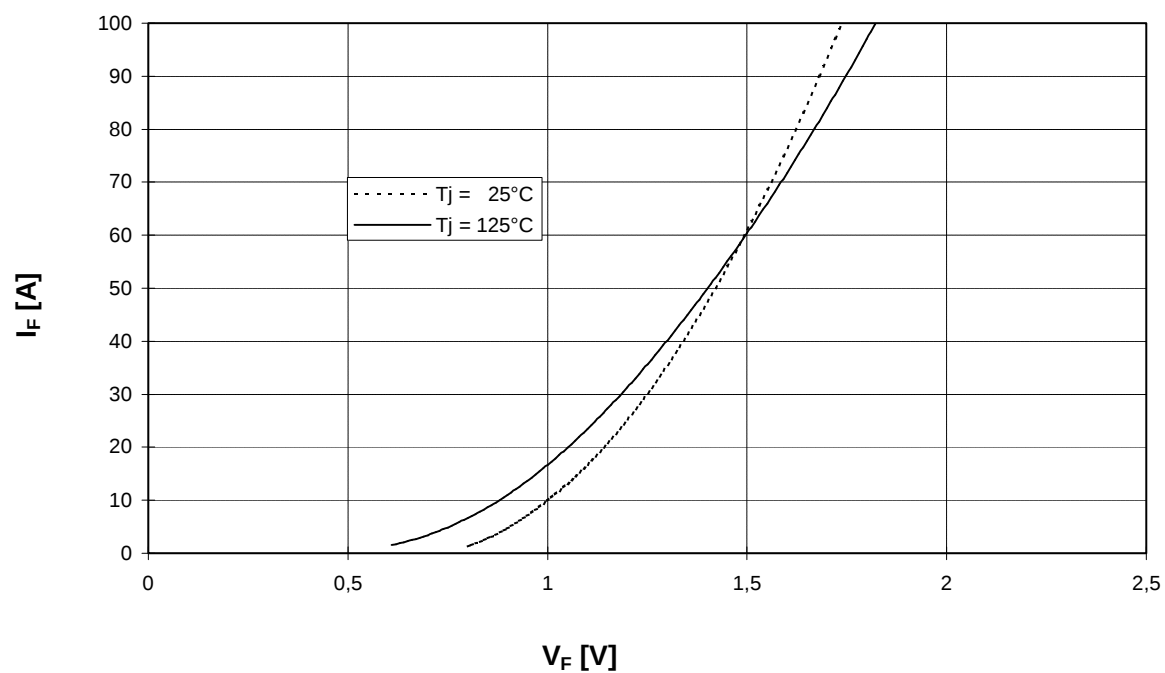
$$V_{GE} = 15 \text{ V}$$

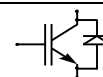


Durchlaßkennlinie der Brems-Chopper-Diode (typisch)

Forward characteristic of brake-chopper-FWD (typical)

$$I_F = f(V_F)$$

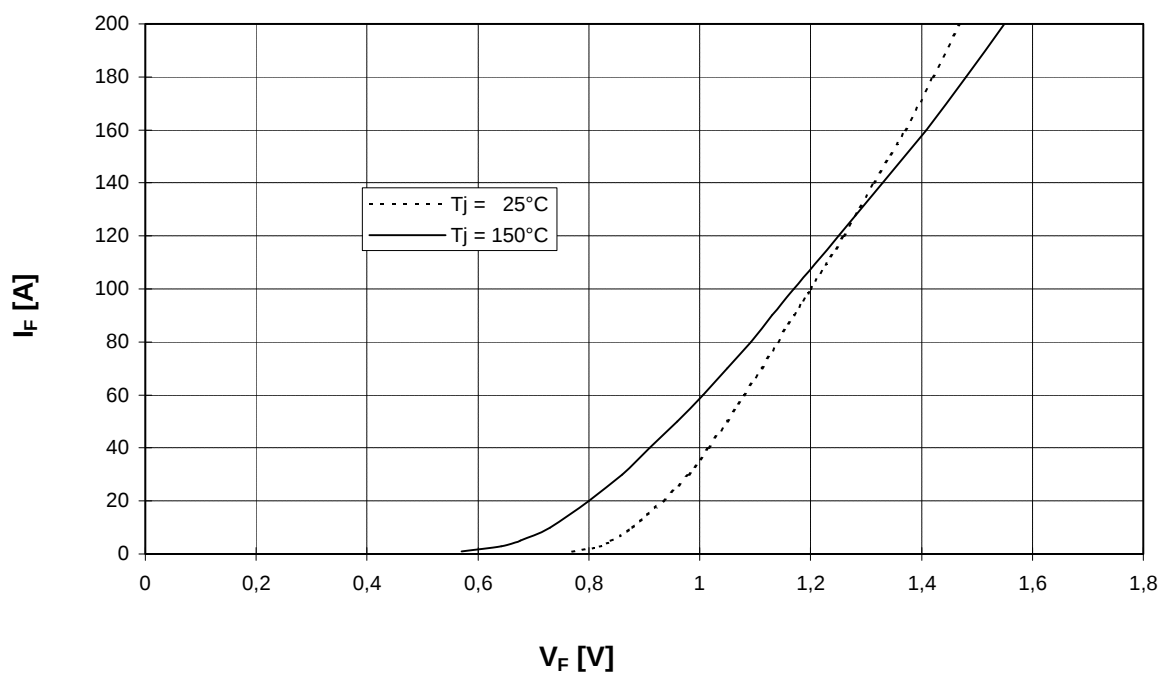




Durchlaßkennlinie der Gleichrichterdiode (typisch)

$$I_F = f(V_F)$$

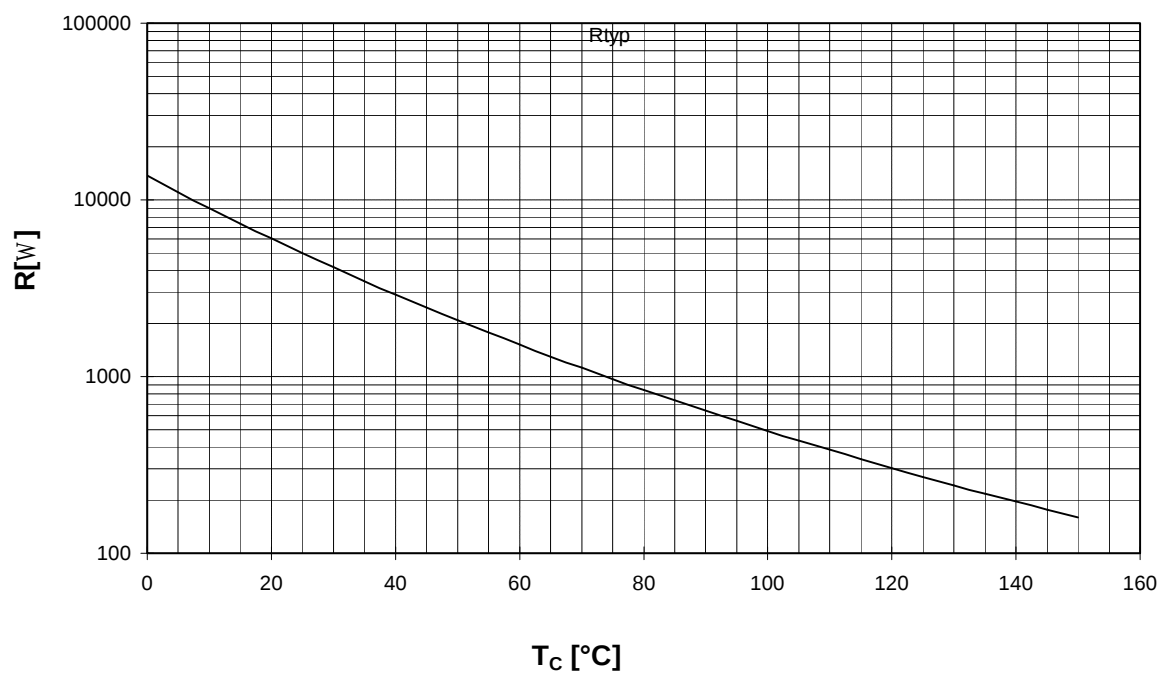
Forward characteristic of Rectifier Diode (typical)

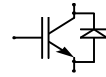


NTC- Temperaturkennlinie (typisch)

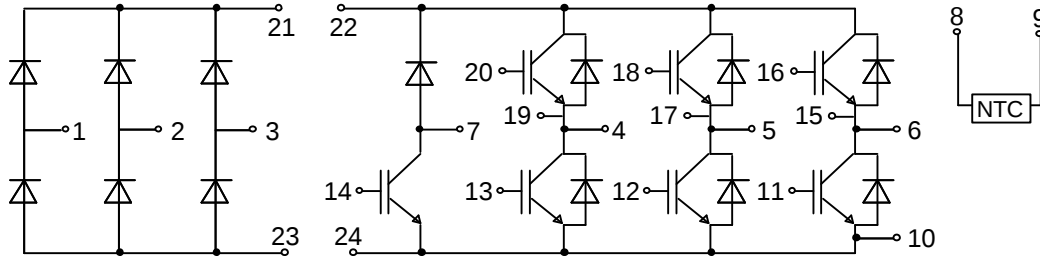
$$R = f(T)$$

NTC- temperature characteristic (typical)

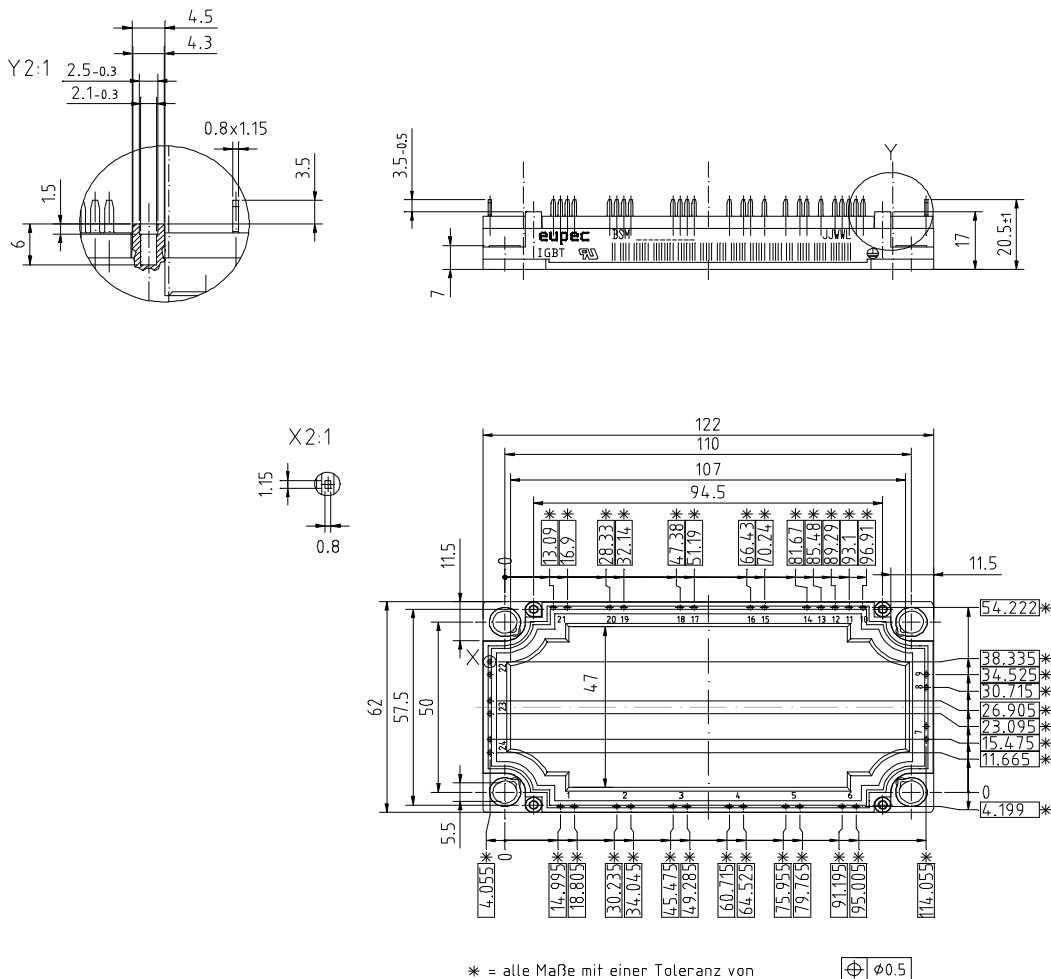




Schaltplan/ Circuit diagram



Gehäuseabmessungen/ Package outlines



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